

**NPN SILICON PLANAR TRANSISTOR**

**FEATURES**

- \* Power dissipation  
P<sub>c</sub>: 0.25 W (T<sub>amb</sub>=25°C)
- \* Collector current  
I<sub>c</sub>: 0.1 A
- \* Collector-base voltage  
V<sub>CB0</sub>: 30 V
- \* Operating and storage junction temperature range  
T<sub>J</sub>, T<sub>stg</sub>: -55°C to +150°C

**MECHANICAL DATA**

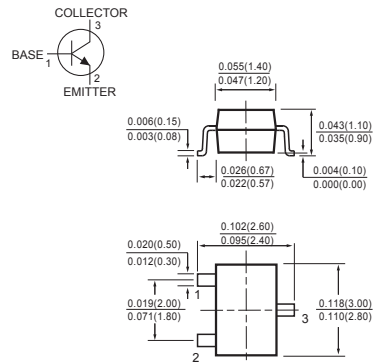
- \* Case: Molded plastic
- \* Epoxy: UL 94V-O rate flame retardant
- \* Lead: MIL-STD-202E method 208C guaranteed
- \* Mounting position: Any
- \* Weight: 0.008 gram

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified.  
Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.



**SOT-23**



Dimensions in inches and (millimeters)

**ABSOLUTE MAXIMUM RATINGS**

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector-base Voltage	V <sub>CB0</sub>	30	V
Collector-emitter Voltage	V <sub>CEO</sub>	30	V
Emitter-base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	I <sub>c</sub>	100	mA
Collector Dissipation	P <sub>c</sub>	250	mW
Operation And Storage Junction	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ELECTRICAL CHARACTERISTICS ( @ TA = 25°C unless otherwise noted )**

CHARACTERISTICS	SYMBOL	MIN	TYP	MAX	UNITS
Collector-base Voltage (I <sub>c</sub> = 100μA, I <sub>E</sub> =0)	V <sub>CB0</sub>	30	-	-	V
Collector-emitter Voltage (I <sub>c</sub> = 1mA, I <sub>B</sub> =0)	V <sub>CEO</sub>	30	-	-	V
Emitter-base Voltage (I <sub>E</sub> = 100μA, I <sub>C</sub> =0)	V <sub>EBO</sub>	5.0	-	-	V
Collector Cut-off Current (V <sub>CB</sub> = 30V, I <sub>E</sub> =0)	I <sub>CB0</sub>	-	-	15	nA
Emitter Cut-off Current (V <sub>EB</sub> = 5V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	500	nA
DC Current Gain (I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V)	h <sub>FE</sub>	150	-	1000	-
Collector-emitter Saturation Voltage (I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA)	V <sub>CE(sat)</sub>	-	-	0.60	V
Base-emitter Voltage (I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA)	V <sub>BE(sat)</sub>	-	-	1.2	V
Transition Frequency (V <sub>CE</sub> = 5V, I <sub>C</sub> = -10mA, f=100MHz)	f <sub>r</sub>	125	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10V, f= 1MHz)	C <sub>ob</sub>	-	-	3.5	pF
Noise Figure (V <sub>CE</sub> = 5V, I <sub>C</sub> = 200μA, f=1KHz)	NF	-	-	4.0	dB

CLASSIFICATION	CMBT9014	B	C	D
h <sub>FE</sub>	150-1000	100-300	200-600	400-1000
Marking	14	14B	14C	14D

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